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ABSTRACT

The present invention is related to methods of fabricating a resistance variable memory element and a device formed therefrom having improved switching characteristics. According to an embodiment of the present invention a resistance variable material memory element is annealed to remove stoichiometric amounts of a component of the resistance variable material. According to another embodiment of the present invention a silver-germanium-selenide glass is annealed for a duration of about 10 minutes in the presence of oxygen to drive off selenium and increase the rigidity of the glass.